N-Channel 20-V (D-S) MOSFET

Key Features:

- Low r_{DS(on)} trench technology
- · Low thermal impedance
- · Fast switching speed

Typical Applications:

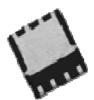
- · White LED boost converters
- Automotive Systems
- Industrial DC/DC Conversion Circuits

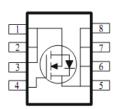
PRODUCT SUMMARY			
V _{DS} (V)	$r_{DS(on)}(m\Omega)$	I⊳(A)	
20	$2.5 @ V_{GS} = 4.5V$	37	
20	$4 @ V_{GS} = 2.5V$	29	



FREE







ABSOLUTE MAXIMUM RATINGS ($T_A = 25^{\circ}$ C UNLESS OTHERWISE NOTED)							
Parameter	Symbol	Limit	Units				
Drain-Source Voltage			20	V			
Gate-Source Voltage		V_{GS}	±8	V			
Continuous Drain Current a	T _A =25°C	· I _D	37				
Continuous Diairi Curient	T _A =70°C		29	Α			
Pulsed Drain Current ^b		I _{DM}	50				
Continuous Source Current (Diode Conduction) a		I _S	8.1	Α			
Power Dissipation ^a	T _A =25°C	P_{D}	5	W			
Fower Dissipation	T _A =70°C	' D	3.2	VV			
Operating Junction and Storage Temperature Range		T_J,T_stg	-55 to 150	°C			

THERMAL RESISTANCE RATINGS							
Parameter			Maximum	Units			
Maximum Junction-to-Ambient ^a	t <= 10 sec	$R_{\theta JA}$	25	°C/W			
Maximum Junction-to-Ambient	Steady State	IΛθJA	65	C/VV			

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Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

Electrical Characteristics

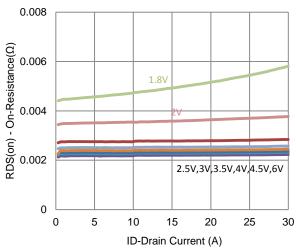
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250 \text{ uA}$	0.4			V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$			±100	nA	
Zero Gate Voltage Drain Current	lana	$V_{DS} = 16 \text{ V}, V_{GS} = 0 \text{ V}$	1		1	uA	
Zero Gate Voltage Brain Gurrent	I _{DSS}	$V_{DS} = 16 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			25	uA	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} = 5 \text{ V}, V_{GS} = 4.5 \text{ V}$	30			Α	
Drain-Source On-Resistance ^a	r	$V_{GS} = 4.5 \text{ V}, I_D = 20 \text{ A}$	2.5		2.5	mΩ	
Drain-Source On-Resistance	r _{DS(on)}	$V_{GS} = 2.5 \text{ V}, I_D = 16 \text{ A}$			4	11122	
Forward Transconductance ^a	g _{fs}	$V_{DS} = 15 \text{ V}, I_{D} = 20 \text{ A}$		32		S	
Diode Forward Voltage ^a	V_{SD}	$I_{S} = 4.1 \text{ A}, V_{GS} = 0 \text{ V}$		0.66		V	
		Dynamic ^b					
Total Gate Charge	Q_g	$V_{DS} = 10 \text{ V}, V_{GS} = 4.5 \text{ V},$		105			
Gate-Source Charge	Q_{gs}	$I_{DS} = 10 \text{ V}, V_{GS} = 4.3 \text{ V},$ $I_{D} = 20 \text{ A}$		15		nC	
Gate-Drain Charge	Q_gd	10 - 20 A		34			
Turn-On Delay Time	t _{d(on)}	$V_{DS} = 10 \text{ V}, R_{L} = 0.5 \Omega,$		48			
Rise Time	t _r	$V_{DS} = 10 \text{ V}, K_L - 0.3 \Omega,$ $I_D = 20 \text{ A},$		99		ne	
Turn-Off Delay Time	$t_{d(off)}$	$V_{GEN} = 4.5 \text{ V}, R_{GEN} = 6 \Omega$		356		ns	
Fall Time	t _f	V GEN - 4.5 V, T GEN - 0 12		160			
Input Capacitance	C _{iss}			18307			
Output Capacitance	C _{oss}	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		1505		pF	
Reverse Transfer Capacitance	C_{rss}			1081			

Notes

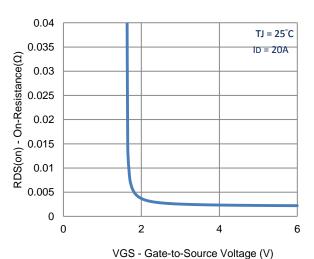
- Pulse test: PW <= 300us duty cycle <= 2%.
- Guaranteed by design, not subject to production testing. b.

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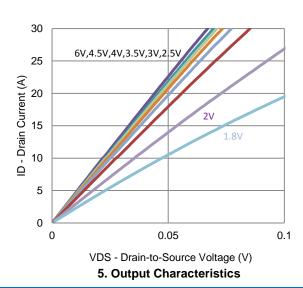
Typical Electrical Characteristics

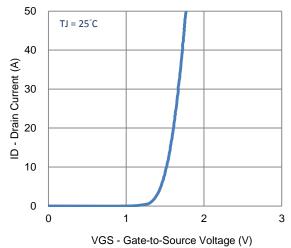


1. On-Resistance vs. Drain Current

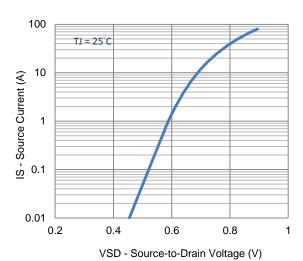


3. On-Resistance vs. Gate-to-Source Voltage

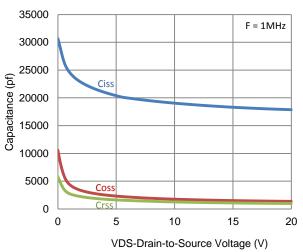




2. Transfer Characteristics

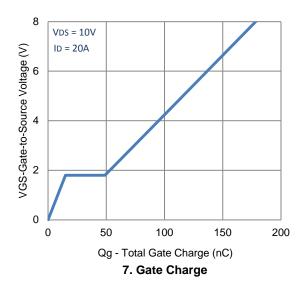


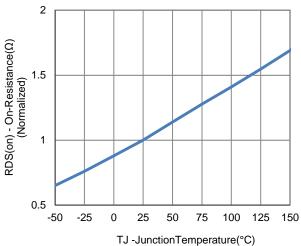
4. Drain-to-Source Forward Voltage

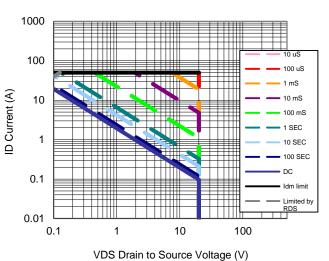


6. Capacitance

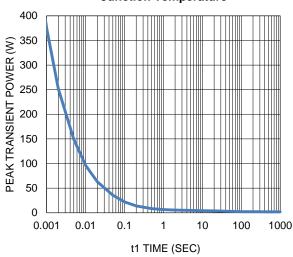
Typical Electrical Characteristics





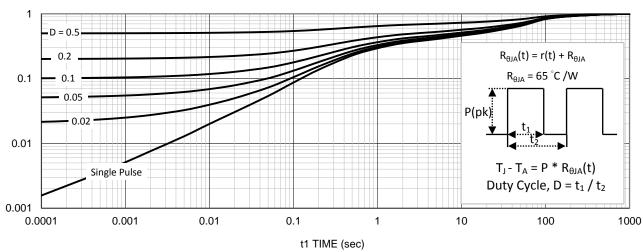


8. Normalized On-Resistance Vs Junction Temperature



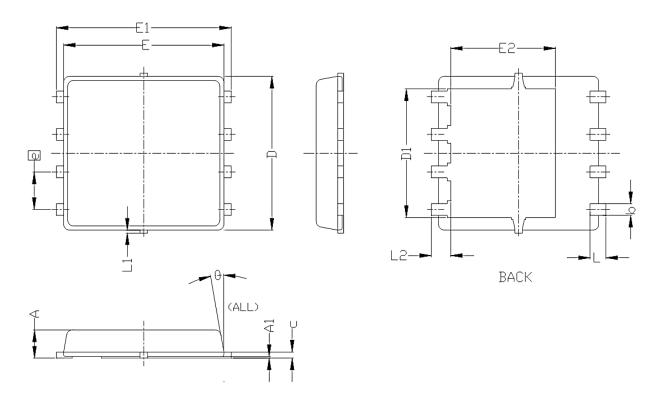
9. Safe Operating Area

10. Single Pulse Maximum Power Dissipation



11. Normalized Thermal Transient Junction to Ambient

Package Information



SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES			
	MIN	NOM	MAX	MIN	NOM	MAX	
Α	0.85	0. 95	1.00	0.033	0.037	0. 039	
Al	0.00		0.05	0.000		0.002	
b	0.30	0.40	0.50	0.012	0.016	0.020	
c	0.15	0. 20	0. 25	0.006	0.008	0.010	
D	5. 20 BSC			0. 205 BSC			
D1	4. 35 BSC			0. 171 BSC			
E		5.55 BSC			0.219 BSC		
E1	6. 05 BSC			0. 238 BSC			
E2	3. 62 BSC			0. 143 BSC			
e	1. 27 BSC		0.050 BSC				
L	0.45	0.55	0.65	0.018	0.022	0.026	
L1	0		0. 15	0		0.006	
L2	0.68 REF			0. 027 REF			
θ	0°		10°	0°		10°	